

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 02-162717

(43)Date of publication of application : 22.06.1990

(51)Int.Cl.

H01L 21/20
H01L 21/205
H01L 29/203
H01S 3/18

(21)Application number : 63-318824

(71)Applicant : FUJITSU LTD

(22)Date of filing : 15.12.1988

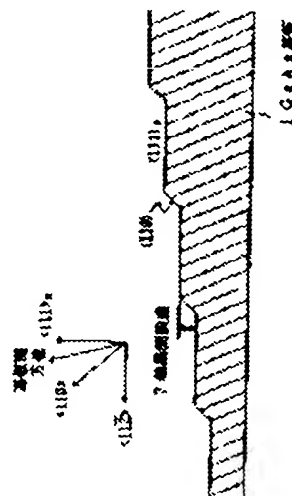
(72)Inventor : KODAMA KUNIHIKO

(54) FORMATION OF QUANTUM FINE WIRE

(57)Abstract:

PURPOSE: To form the arrangement of a quantum fine wire, having the width of several atomic layers in the same thickness as the stepping of crystal face, in a highly precise manner by a method wherein a quantum well semiconductor layer, which is epitaxially grown, is formed by controlling its thickness and width smaller than the de Broglie wavelength.

CONSTITUTION: The crystal face of a substrate is formed into a face (111)B which is inclined in orientation $\langle 110 \rangle$. As a result, the substrate surface is turned to the face (111)B having a stepping periodically. The side face constituting the stepping is a face (110). In the first atomic layer epitaxy, a semiconductor layer having a wide forbidden band width, which becomes the barrier of quantum well, is deposited. As it is an isotropic growing method, the stepping on the substrate crystal surface is in the state as it is. When a semiconductor, which becomes a confinement layer, is coated thereon using an anisotropic crystal growth method, no crystal growth progresses on the face (111)B, and crystal growth progresses only on the face (110) of the stepped part. As a result, a confinement layer, having the controlled atomic column number in lateral direction, is formed in the thickness same as the stepping. In the subsequently conducted atomic layer epitaxy, the barrier layer of a quantum well is formed enveloping the formed carrier confinement layer, and a quantum fine line is formed.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Date of first publication of the application]

[Date of extension]

[Date of extinction of right]